Carl-Mikael G Zetterling

List of Publications by Year
in descending order

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149	2,721	186265	289244
papers	citations	28 h-index	40 g-index

151	151	151	1415
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Deposition of diamond films on single crystalline silicon carbide substrates. Diamond and Related Materials, 2020, 101, 107625.	3.9	11
2	A Silicon Carbide 256 Pixel UV Image Sensor Array Operating at 400 Â°C. IEEE Journal of the Electron Devices Society, 2020, 8, 116-121.	2.1	8
3	Wide Bandgap Integrated Circuits for High Power Management in Extreme Environments. , 2020, , 167-178.		0
4	500Â^circC SiC PWM Integrated Circuit. IEEE Transactions on Power Electronics, 2019, 34, 1997-2001.	7.9	9
5	500Â°C SiC-based driver IC for SiC power MOSFETs. , 2019, , .		3
6	Silicon Carbide Bipolar Analog Circuits for Extreme Temperature Signal Conditioning. IEEE Transactions on Electron Devices, 2019, 66, 3764-3770.	3.0	8
7	555-Timer and Comparators Operational at 500 Â°C. IEEE Transactions on Electron Devices, 2019, 66, 3734-3739.	3.0	11
8	Towards Silicon Carbide VLSI Circuits for Extreme Environment Applications. Electronics (Switzerland), 2019, 8, 496.	3.1	20
9	High-Temperature Recessed Channel SiC CMOS Inverters and Ring Oscillators. IEEE Electron Device Letters, 2019, 40, 670-673.	3.9	15
10	Investigation of a Self-Aligned Cobalt Silicide Process for Ohmic Contacts to Silicon Carbide. Journal of Electronic Materials, 2019, 48, 2509-2516.	2.2	2
11	A 4H-SiC BJT as a Switch for On-Chip Integrated UV Photodiode. IEEE Electron Device Letters, 2019, 40, 51-54.	3.9	10
12	15 kV-Class Implantation-Free 4H-SiC BJTs With Record High Current Gain. IEEE Electron Device Letters, 2018, 39, 63-66.	3.9	37
13	Scaling and Modeling of High Temperature 4H-SiC p-i-n Photodiodes. IEEE Journal of the Electron Devices Society, 2018, 6, 139-145.	2.1	5
14	500 Â°C, High Current Linear Voltage Regulator in 4H-SiC BJT Technology. IEEE Electron Device Letters, 2018, 39, 548-551.	3.9	13
15	A 600 Â°C TTL-based 11-stage Ring Oscillator in Bipolar Silicon Carbide Technology. IEEE Electron Device Letters, 2018, , 1-1.	3.9	20
16	Bipolar integrated circuits in SiC for extreme environment operation. Semiconductor Science and Technology, 2017, 32, 034002.	2.0	28
17	A Fully Integrated Silicon-Carbide Sigmaâ€“Delta Modulator Operating up to 500 Â°C. IEEE Transactions on Electron Devices, 2017, 64, 2782-2788.	3.0	14
18	Integration and High-Temperature Characterization of Ferroelectric Vanadium-Doped Bismuth Titanate Thin Films on Silicon Carbide. Journal of Electronic Materials, 2017, 46, 4478-4484.	2.2	4

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19	High Gamma Ray Tolerance for 4H-SiC Bipolar Circuits. IEEE Transactions on Nuclear Science, 2017, 64, 852-858.	2.0	18
20	A Comprehensive Study on the Geometrical Effects in High-Power 4Hâ€“SiC BJTs. IEEE Transactions on Electron Devices, 2017, 64, 882-887.	3.0	4
21	High frequency characteristic of a monolithic 500 Â°C OpAmp-RC integrator in SiC bipolar IC technology. Solid-State Electronics, 2017, 135, 65-70.	1.4	2
22	SiC BJT Compact DC Model With Continuous- Temperature Scalability From 300 to 773 K. IEEE Transactions on Electron Devices, 2017, 64, 3588-3594.	3.0	10
23	500 Â°C High Current 4H-SiC Lateral BJTs for High-Temperature Integrated Circuits. IEEE Electron Device Letters, 2017, 38, 1429-1432.	3.9	22
24	A Wafer-Scale Ni-Salicide Contact Technology on n-Type 4H-SiC. ECS Journal of Solid State Science and Technology, 2017, 6, P197-P200.	1.8	13
25	Material aspects of wide temperature range amplifier design in SiC bipolar technologies. Journal of Materials Research, 2016, 31, 2928-2935.	2.6	2
26	High-temperature passive components for extreme environments. , 2016, , .		8
27	Silicon Carbide Fully Differential Amplifier Characterized Up to 500 Â°C. IEEE Transactions on Electron Devices, 2016, 63, 2242-2247.	3.0	21
28	State of the art power switching devices in SiC and their applications. , 2016, , .		5
29	Intertwined Design: A Novel Lithographic Method to Realize Area Efficient High-Voltage SiC BJTs and Darlington Transistors. IEEE Transactions on Electron Devices, 2016, 63, 4366-4372.	3.0	6
30	A 500 Â°C 8-b Digital-to-Analog Converter in Silicon Carbide Bipolar Technology. IEEE Transactions on Electron Devices, 2016, 63, 3445-3450.	3.0	15
31	Wide temperature range integrated amplifier in bipolar 4H-SiC technology. , 2016, , .		2
32	550 Â°C 4H-SiC p-i-n Photodiode Array With Two-Layer Metallization. IEEE Electron Device Letters, 2016, 37, 1594-1596.	3.9	24
33	Wide Temperature Range Integrated Bandgap Voltage References in 4Hâ€“SiC. IEEE Electron Device Letters, 2016, 37, 146-149.	3.9	22
34	A study on positive-feedback configuration of a bipolar SiC high temperature operational amplifier. Solid-State Electronics, 2016, 116, 33-37.	1.4	16
35	Integrated circuits in silicon carbide for high-temperature applications. MRS Bulletin, 2015, 40, 431-438.	3.5	40
36	Influence of Passivation Oxide Thickness and Device Layout on the Current Gain of SiC BJTs. IEEE Electron Device Letters, 2015, 36, 11-13.	3.9	24

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37	5.8-kV Implantation-Free 4H-SiC BJT With Multiple-Shallow-Trench Junction Termination Extension. IEEE Electron Device Letters, 2015, 36, 168-170.	3.9	25
38	Single-step synthesis process of Ti 3 SiC 2 ohmic contacts on 4H-SiC by sputter-deposition of Ti. Scripta Materialia, 2015, 99, 53-56.	5.2	30
39	Conductivity modulated on-axis 4H-SiC 10+ kV PiN diodes. , 2015, , .		18
40	500 Â°C Bipolar SiC Linear Voltage Regulator. IEEE Transactions on Electron Devices, 2015, 62, 1953-1957.	3.0	30
41	Optimal Emitter Cell Geometry in High Power 4H-SiC BJTs. IEEE Electron Device Letters, 2015, 36, 1069-1072.	3.9	9
42	Area- and efficiency-optimized junction termination for a 5.6 kV SiC BJT process with low ON-resistance. , 2015, , .		13
43	A monolithic SiC drive circuit for SiC Power BJTs. , 2015, , .		15
44	SiC Etching and Sacrificial Oxidation Effects on the Performance of 4H-SiC BJTs. Materials Science Forum, 2014, 778-780, 1005-1008.	0.3	18
45	Characterization of La_xHf_yO Gate Dielectrics in 4H-SiC MOS Capacitor. Materials Science Forum, 2014, 778-780, 549-552.	0.3	2
46	A Monolithic, 500 Â°C Operational Amplifier in 4H-SiC Bipolar Technology. IEEE Electron Device Letters, 2014, 35, 693-695.	3.9	63
47	Effects of 3-MeV Protons on 4H-SiC Bipolar Devices and Integrated OR-NOR Gates. IEEE Transactions on Nuclear Science, 2014, 61, 1772-1776.	2.0	9
48	Lateral p-n-p Transistors and Complementary SiC Bipolar Technology. IEEE Electron Device Letters, 2014, 35, 428-430.	3.9	17
49	500$^{circ}{m C}$ Bipolar Integrated OR/NOR Gate in 4H-SiC. IEEE Electron Device Letters, 2013, 34, 1091-1093.	3.9	80
50	Process Variation Tolerant 4H-SiC Power Devices Utilizing Trench Structures. Materials Science Forum, 2013, 740-742, 809-812.	0.3	1
51	High-Temperature Characterization of 4H-SiC Darlington Transistors for Low Voltage Applications. Materials Science Forum, 2013, 740-742, 966-969.	0.3	2
52	Effects of 3 MeV protons on 4H-SiC bipolar devices and integrated OR-NOR gates. , 2013, , .		0
53	Metal Work-function and Doping-Concentration Dependent Barrier Height of Ni-Contacts to 4H-SiC with Metal-Embedded Nano-Particles. Materials Science Forum, 2012, 717-720, 857-860.	0.3	3
54	Investigation of Current Gain Degradation in 4H-SiC Power BJTs. Materials Science Forum, 2012, 717-720, 1131-1134.	0.3	1

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55	Present and future applications of Silicon Carbide devices and circuits. , 2012, , .		14
56	Growth and characterization of epitaxial Ti3GeC2 thin films on 4H-SiC(0001). Journal of Crystal Growth, 2012, 343, 133-137.	1.5	9
57	Future high temperature applications for SiC integrated circuits. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 1647-1650.	0.8	16
58	Design and Characterization of High-Temperature ECL-Based Bipolar Integrated Circuits in 4H-SiC. IEEE Transactions on Electron Devices, 2012, 59, 1076-1083.	3.0	56
59	Removal of Crystal Orientation Effects on the Current Gain of 4H-SiC BJTs Using Surface Passivation. IEEE Electron Device Letters, 2011, 32, 596-598.	3.9	6
60	Effect of annealing temperature on the barrier height of nano-particle embedded Ni-contacts to 4H-SiC. , 2011, , .		1
61	Surface-Passivation Effects on the Performance of 4H-SiC BJTs. IEEE Transactions on Electron Devices, 2011, 58, 259-265.	3.0	57
62	Modeling and Characterization of the on-Resistance in 4H-SiC Power BJTs. IEEE Transactions on Electron Devices, 2011, 58, 2081-2087.	3.0	20
63	High-Voltage (2.8 kV) Implantation-Free 4H-SiC BJTs With Long-Term Stability of the Current Gain. IEEE Transactions on Electron Devices, 2011, 58, 2665-2669.	3.0	26
64	SiC power devices — Present status, applications and future perspective. , 2011, , .		223
65	SiC bipolar devices for high power and integrated drivers. , 2011, , .		5
66	Ohmic contact properties of magnetron sputtered Ti3SiC2 on n- and p-type 4H-silicon carbide. Applied Physics Letters, 2011, 98, .	3.3	67
67	High Voltage, Low On-Resistance 4H-SiC BJTs with Improved Junction Termination Extension. Materials Science Forum, 2011, 679-680, 706-709.	0.3	8
68	(Invited) Silicon Carbide Bipolar Power Devices. ECS Transactions, 2011, 41, 189-200.	0.5	0
69	Measurements and Simulations of Lateral PNP Transistors in a SiC NPN BJT Technology for High Temperature Integrated Circuits. Materials Science Forum, 2011, 679-680, 758-761.	0.3	1
70	Toward 4H-SiC MISFETs Devices Based on ONO (SiO2-Si3N4-SiO2) Structures. Journal of the Electrochemical Society, 2011, 158, H496.	2.9	6
71	Current Gain Degradation in 4H-SiC Power BJTs. Materials Science Forum, 2011, 679-680, 702-705.	0.3	4
72	Modeling and Characterization of Current Gain Versus Temperature in 4H-SiC Power BJTs. IEEE Transactions on Electron Devices, 2010, 57, 704-711.	3.0	56

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73	Influence of Emitter Width and Emitterâ€“Base Distance on the Current Gain in 4H-SiC Power BJTs. IEEE Transactions on Electron Devices, 2010, 57, 2664-2670.	3.0	26
74	Experimental Evaluation of Different Passivation Layers on the Performance of 3kV 4H-SiC BJTs. Materials Science Forum, 2010, 645-648, 661-664.	0.3	7
75	Temperature Modeling and Characterization of the Current Gain in 4H-SiC Power BJTs. Materials Science Forum, 2010, 645-648, 1061-1064.	0.3	0
76	SiC Bipolar Power Transistors - Design and Technology Issues for Ultimate Performance. Materials Research Society Symposia Proceedings, 2010, 1246, 1.	0.1	5
77	Optimization of Poly-silicon Process for 3C-SiC Based MOS Devices. Materials Research Society Symposia Proceedings, 2010, 1246, 1.	0.1	0
78	Electrical properties of MOS structures based on 3C-SiC(111) epilayers grown by Vapor-Liquid-Solid Transport and Chemical-Vapor Deposition on 6H-SiC(0001). AIP Conference Proceedings, 2010, , .	0.4	1
79	Influence of crystal orientation on the current gain in 4H-SiC BJTs. , 2010, , .		0
80	Comparative study of thermally grown oxides on n-type free standing 3C-SiC (001). Journal of Applied Physics, 2009, 106, 044513.	2.5	15
81	Advanced oxidation process combining oxide deposition and short postoxidation step for N-type 3C- and 4H-SiC. Journal of Applied Physics, 2009, 106, 044514.	2.5	17
82	High-Voltage 4H-SiC PiN Diodes With Etched Junction Termination Extension. IEEE Electron Device Letters, 2009, 30, 1170-1172.	3.9	55
83	Implantation-Free Low On-Resistance 4H-SiC BJTs with Common-Emitter Current Gain of 50 and High Blocking Capability. Materials Science Forum, 2009, 615-617, 833-836.	0.3	7
84	Simulations of Open Emitter Breakdown Voltage in SiC BJTs with Non Implanted JTE. Materials Science Forum, 2009, 615-617, 841-844.	0.3	4
85	Low-Forward-Voltage-Drop 4H-SiC BJTs Without Base Contact Implantation. IEEE Transactions on Electron Devices, 2008, 55, 1907-1911.	3.0	14
86	High-Current-Gain SiC BJTs With Regrown Extrinsic Base and Etched JTE. IEEE Transactions on Electron Devices, 2008, 55, 1894-1898.	3.0	18
87	Corrections to "Low-Forward-Voltage-Drop 4H-SiC BJTs Without Base Contact Implantation". IEEE Transactions on Electron Devices, 2008, 55, 2531-2531.	3.0	2
88	Fabrication of 2700-V 12-$hbox{m}Omega cdot hbox{cm}^{2}$ Non Ion-Implanted 4H-SiCBJTs With Common-Emitter Current Gain of 50. IEEE Electron Device Letters, 2008, 29, 1135-1137.	3.9	35
89	Surface passivation oxide effects on the current gain of 4H-SiC bipolar junction transistors. Applied Physics Letters, 2008, 92, 082113.	3.3	25
90	Analysis of the base current and saturation voltage in 4H-SiC power BJTs. , 2007, , .		1

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91	Influence of the base contact on the electrical characteristics of SiC BJTs. , 2007, , .		4
92	Simultaneous study of nickel based ohmic contacts to Si-face and C-face of n-type silicon carbide. , 2007, , .		0
93	1200-V 5.2-$hbox{m}Omegacdothbox{cm}^{2}$ 4H-SiC BJTs With a High Common-Emitter Current Gain. IEEE Electron Device Letters, 2007, 28, 1007-1009.	3.9	46
94	Geometrical effects in high current gain 1100-V 4H-SiC BJTs. IEEE Electron Device Letters, 2005, 26, 743-745.	3.9	53
95	Ferroelectric thin films on silicon carbide for next-generation nonvolatile memory and sensor devices. Thin Solid Films, 2004, 469-470, 444-449.	1.8	15
96	<title>Thin films in silicon carbide semiconductor devices</title>. , 2004, , .		0
97	Investigation of thermal properties in fabricated 4H-SiC high power bipolar transistors. Solid-State Electronics, 2003, 47, 639-644.	1.4	5
98	Ferroelectric Pb(Zr0.52Ti0.48)/SiC field-effect transistor. Applied Physics Letters, 2003, 83, 3975-3977.	3.3	21
99	Processing and Properties of Ferroelectric Pb(Zr,Ti)O 3 /Silicon Carbide Field-Effect Transistor. Integrated Ferroelectrics, 2003, 57, 1221-1231.	0.7	0
100	Combination of JFET and MOSFET devices in 4H-SiC for high-temperature stable circuit operation. Electronics Letters, 2003, 39, 933.	1.0	2
101	Ferroelectric Pb(Zr,Ti)O3/Al2O3/4Hâ€“SiC diode structures. Applied Physics Letters, 2002, 81, 895-897.	3.3	14
102	Characterization of heterojunction diodes with hydride vapor phase epitaxy grown AlGaN on 4Hâ€“SiC. Journal of Applied Physics, 2002, 91, 2372-2379.	2.5	21
103	Ohmic contact formation on inductively coupled plasma etched 4H-silicon carbide. Journal of Electronic Materials, 2002, 31, 340-345.	2.2	9
104	Low resistivity ohmic contacts on 4H-silicon carbide for high power and high temperature device applications. Microelectronic Engineering, 2002, 60, 261-268.	2.4	31
105	The influence of band offsets on the IV characteristics for GaN/SiC heterojunctions. Solid-State Electronics, 2002, 46, 827-835.	1.4	18
106	Electrical characteristics of metal-oxide-semiconductor capacitors on plasma etch-damaged silicon carbide. Solid-State Electronics, 2002, 46, 1375-1380.	1.4	10
107	Reduction of the Schottky barrier height on silicon carbide using Au nano-particles. Solid-State Electronics, 2002, 46, 1433-1440.	1.4	69
108	Microscopic mapping of specific contact resistances and long-term reliability tests on 4H-silicon carbide using sputtered titanium tungsten contacts for high temperature device applications. Journal of Applied Physics, 2002, 92, 253-260.	2.5	10

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109	Schottky barrier height dependence on the metal work function for p-type 4H-silicon carbide. Journal of Electronic Materials, 2001, 30, 242-246.	2.2	42
110	Inductively coupled plasma etch damage in 4Hâ˜SiC investigated by Schottky diode characterization. Journal of Electronic Materials, 2001, 30, 247-252.	2.2	22
111	Fabrication and characterization of heterojunction diodes with HVPE-grown GaN on 4H-SiC. IEEE Transactions on Electron Devices, 2001, 48, 444-449.	3.0	26
112	High density plasma via hole etching in SiC. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2001, 19, 1878-1881.	2.1	31
113	Low resistivity ohmic titanium carbide contacts to n- and p-type 4H-silicon carbide. Solid-State Electronics, 2000, 44, 1179-1186.	1.4	48
114	Structural and electrical characteristics of oxygen-implanted 6H-SiC. Nuclear Instruments & Methods in Physics Research B, 2000, 169, 1-5.	1.4	7
115	Electrical characterization of TiC ohmic contacts to aluminum ion implanted 4Hâ€“silicon carbide. Applied Physics Letters, 2000, 77, 1478-1480.	3.3	32
116	Effect of UV light irradiation on SiC dry etch rates. Journal of Electronic Materials, 2000, 29, 342-346.	2.2	7
117	CVD-based tungsten carbide schottky contacts to 6H-SiC for very high-temperature operation. Journal of Electronic Materials, 2000, 29, 372-375.	2.2	28
118	Investigation of damage behaviour and isolation effect of n-type 6H-SiC by implantation of oxygen. Journal Physics D: Applied Physics, 2000, 33, 1551-1555.	2.8	6
119	Ultradeep, low-damage dry etching of SiC. Applied Physics Letters, 2000, 76, 739-741.	3.3	57
120	Schottky diode formation and characterization of titanium tungsten to n- and p-type 4H silicon carbide. Journal of Applied Physics, 2000, 87, 8039-8044.	2.5	43
121	Via-hole etching for SiC. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1999, 17, 2050.	1.6	34
122	UVâ€“ozone precleaning and forming gas annealing applied to wet thermal oxidation of p-type silicon carbide. Materials Science in Semiconductor Processing, 1999, 2, 23-27.	4.0	8
123	Simulation and electrical characterization of GaN/SiC and AlGaN/SiC heterodiodes. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1999, 61-62, 320-324.	3.5	9
124	A study of optical characteristics of damage in oxygen-implanted 6H-SiC. Journal of Materials Science Letters, 1999, 18, 979-982.	0.5	2
125	Plasma chemistries for high density plasma etching of SiC. Journal of Electronic Materials, 1999, 28, 196-201.	2.2	31
126	Growth of SiC Thin Films on (100) and (111) Silicon by Pulsed Laser Deposition Combined with a Vacuum Annealing Process. Materials Research Society Symposia Proceedings, 1999, 572, 207.	0.1	0

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127	Simulation Study of on-state Losses as Function of Carrier Life-time for a GaN/SiC High Power HBT Design. Physica Scripta, 1999, T79, 290.	2.5	5
128	High rate etching of SiC and SiCN in NF3 inductively coupled plasmas. Solid-State Electronics, 1998, 42, 743-747.	1.4	23
129	Junction barrier Schottky diodes in 6H SiC. Solid-State Electronics, 1998, 42, 1757-1759.	1.4	15
130	ICP etching of SiC. Solid-State Electronics, 1998, 42, 2283-2288.	1.4	44
131	Inductively coupled plasma etching of bulk 6H-SiC and thin-film SiCN in NF3 chemistries. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1998, 16, 2204-2209.	2.1	57
132	Influence of growth conditions on electrical characteristics of AlN on SiC. Applied Physics Letters, 1997, 70, 3549-3551.	3.3	31
133	Investigation of aluminum nitride grown by metalâ€“organic chemical-vapor deposition on silicon carbide. Journal of Applied Physics, 1997, 82, 2990-2995.	2.5	65
134	Formation and High Frequency CV-Measurements of Aluminum / Aluminum Nitride / 6H Silicon Carbide Structures. Materials Research Society Symposia Proceedings, 1996, 423, 667.	0.1	14
135	A novel UMOS capacitor test structure for SiC devices. Solid-State Electronics, 1996, 39, 1396-1397.	1.4	3
136	Thermal oxidation of n- and p-type 6H-silicon carbide. Physica Scripta, 1994, T54, 291-293.	2.5	9
137	Comparison of Thermal Gate Oxides on Silicon and Carbon Face P-Type 6H Silicon Carbide. Materials Research Society Symposia Proceedings, 1994, 339, 209.	0.1	7
138	Temperature stability of cobalt Schottky contacts on n- and p-type 6H silicon carbide. Applied Surface Science, 1993, 73, 316-321.	6.1	34
139	SiC device technology for high voltage and RF power applications. , 0, , .		2
140	Measurements and simulations of self-heating and switching with 4H-SiC power BJTs. , 0, , .		3
141	Thermal-issues for design of high power SiC MESFETs. , 0, , .		2
142	Silicon carbide devices and processes - present status and future pers. , 0, , .		2
143	Comparative Study of Thermal Oxides and Post-Oxidized Deposited Oxides on n-Type Free Standing 3C-SiC. Materials Science Forum, 0, 645-648, 829-832.	0.3	1
144	Bipolar Integrated OR-NOR Gate in 4H-SiC. Materials Science Forum, 0, 717-720, 1257-1260.	0.3	2

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145	Local Anodic Oxidation of Phosporous-Implanted 4H-SiC by Atomic Force Microscopy. Materials Science Forum, 0, 717-720, 905-908.	0.3	3
146	Area-Optimized JTE for 4.5 kV Non Ion-Implanted 4H-SiC BJT. Materials Science Forum, 0, 740-742, 974-977.	0.3	8
147	Fabrication and Design of 10 kV PiN Diodes Using On-Axis 4H-SiC. Materials Science Forum, 0, 778-780, 836-840.	0.3	6
148	Characterization of Ohmic Ni/Ti/Al and Ni Contacts to 4H-SiC from -40Â°C to 500Â°C. Materials Science Forum, 0, 778-780, 681-684.	0.3	8
149	Ultrafast Pulsed <i>I-V</i> and Charge Pumping Interface Characterization of Low-Voltage <i>n</i>-Channel SiC MOSFETs. Materials Science Forum, 0, 1004, 642-651.	0.3	1